

Satoru Matsumoto

List of Publications by Year in descending order

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citing authors

#	ARTICLE	IF	CITATIONS
1	Advanced Industrial Tunnel Oxide Passivated Contact Solar Cell by the Rear-Side Local Carrier-Selective Contact. IEEE Transactions on Electron Devices, 2022, 69, 2481-2487.	3.0	4
2	Bifacial Heterojunction Back Contact Solar Cell: 29-mW/cm ² Output Power Density in Standard Albedo Condition. IEEE Transactions on Electron Devices, 2021, 68, 5645-5651.	3.0	5
3	Optimization of Front Diffusion Profile in Bifacial Interdigitated Back Contact Solar Cell. IEEE Journal of Photovoltaics, 2020, 10, 1582-1590.	2.5	7
4	Bifacial PERC Solar Cell Designs: Bulk and Rear Properties and Illumination Condition. IEEE Journal of Photovoltaics, 2020, 10, 1538-1544.	2.5	11
5	Influence of sputtering power on properties of ZnO thin films fabricated by RF sputtering in room temperature. Science China Information Sciences, 2012, 55, 951-955.	4.3	11
6	Fabrication and characteristics of ZnO thin films deposited by RF sputtering on plastic substrates for flexible display. Science China Information Sciences, 2012, 55, 1441-1445.	4.3	4
7	Boron diffusion behavior in silicon during shallow p ⁺ /n junction formation by non-melt excimer laser annealing. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 1646-1651.	1.8	15
8	Comparison of boron diffusion in silicon during shallow p ⁺ /n junction formation by non-melt excimer and green laser annealing. Physica Status Solidi (A) Applications and Materials Science, 2011, 208, 2772-2777.	1.8	15
9	Epitaxial growth and characterization of BP on Si(100) substrate for use in c-GaN study. Materials Research Society Symposia Proceedings, 2005, 891, 1.	0.1	0
10	Self-Diffusion in Intrinsic and Extrinsic Silicon Using Isotopically Pure ³⁰ Si Layer. Materials Research Society Symposia Proceedings, 2001, 669, 1.	0.1	1
11	Characterization of ultraviolet excited Br [•] -radical etching of InGaAs/InAlAs material system. Journal of Applied Physics, 1996, 79, 4407.	2.5	0
12	Low Voltage and High Speed LSI Operated at Low Temperature. IEEE Transactions on Electronics, Information and Systems, 1994, 114, 217-222.	0.2	0
13	Effect of Melt Stoichiometry on Carrier Concentration Profiles of Silicon Diffusion in Undoped LEC Si-GaAs. Journal of the Electrochemical Society, 1989, 136, 1165-1168.	2.9	3
14	The Mechanism of KINK in MOSFET at Very Low Temperature. IEEE Transactions on Electronics, Information and Systems, 1989, 109, 764-768.	0.2	0
15	Effects of controlled As pressure annealing on deep levels of liquid-encapsulated Czochralski GaAs single crystals. Journal of Applied Physics, 1988, 64, 3987-3993.	2.5	23
16	Effect of carbon concentration on the thermal conversion of liquid-encapsulated Czochralski semi-insulating GaAs. Applied Physics Letters, 1988, 53, 1054-1055.	3.3	16
17	Phosphorus Doping into Silicon Using ArF Excimer Laser. Journal of the Electrochemical Society, 1988, 135, 1030-1032.	2.9	13
18	Growth Mechanism of Direct Writing of Silicon in AR+ Laser CVD. Materials Research Society Symposia Proceedings, 1988, 129, 189.	0.1	0

#	ARTICLE	IF	CITATIONS
19	Two-dimensional analysis of thermal oxidation of silicon. Electronics and Communications in Japan, 1987, 70, 90-98.	0.2	0
20	Formation of Shallow Junction of Boron Using Excimer Laser. The Review of Laser Engineering, 1986, 14, 686-692.	0.0	0
21	The effect of Fowler-Nordheim tunneling current on thin SiO ₂ metal-oxide-semiconductor capacitors. Journal of Applied Physics, 1985, 57, 2072-2076.	2.5	16
22	Effect of Dopant Concentration on the Growth of Oxide Precipitates in Silicon. Materials Research Society Symposia Proceedings, 1984, 36, 263.	0.1	2
23	The Enhanced Diffusion of Arsenic and Phosphorus in Silicon by Thermal Oxidation. Journal of the Electrochemical Society, 1982, 129, 644-648.	2.9	50
24	High Temperature and Short Time Thermal Annealing of Ion-Implanted Silicon. Shinku/Journal of the Vacuum Society of Japan, 1982, 25, 788-794.	0.2	0
25	Carrier Concentration and Hall Mobility in Heavily Arsenic-Diffused Silicon. Journal of the Electrochemical Society, 1980, 127, 1650-1652.	2.9	8
26	Effects of Diffusion-Induced Strain and Dislocation on Phosphorus Diffusion into Silicon. Journal of the Electrochemical Society, 1978, 125, 1840-1845.	2.9	14
27	Concentration Dependence of a Diffusion Coefficient at Phosphorus Diffusion in Germanium. Journal of the Electrochemical Society, 1978, 125, 1307-1309.	2.9	34
28	Phosphorus Diffusion in Silicon Free from the Surface Effect under Extrinsic Conditions. Japanese Journal of Applied Physics, 1975, 14, 1665-1672.	1.5	10